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Kind regards,

Team Nexperia

Unbuffered inverter
Rev. 13 — 12 December 2016

Product data sheet

1. **General description**

The 74LVC1GU04 is a single unbuffered inverter.

The input can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Features and benefits 2.

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- ESD protection:
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Input accepts voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

| Type number | Package | | | |
|--------------|-------------------|--------|--|----------|
| | Temperature range | Name | Description | Version |
| 74LVC1GU04GW | -40 °C to +125 °C | TSSOP5 | plastic thin shrink small outline package; 5 leads; body width 1.25 mm | SOT353-1 |
| 74LVC1GU04GV | -40 °C to +125 °C | SC-74A | plastic surface-mounted package; 5 leads | SOT753 |
| 74LVC1GU04GM | -40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm | SOT886 |
| 74LVC1GU04GF | -40 °C to +125 °C | XSON6 | plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm | SOT891 |
| 74LVC1GU04GN | -40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm | SOT1115 |
| 74LVC1GU04GS | -40 °C to +125 °C | XSON6 | extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm | SOT1202 |
| 74LVC1GU04GX | −40 °C to +125 °C | X2SON5 | X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm | SOT1226 |



Unbuffered inverter

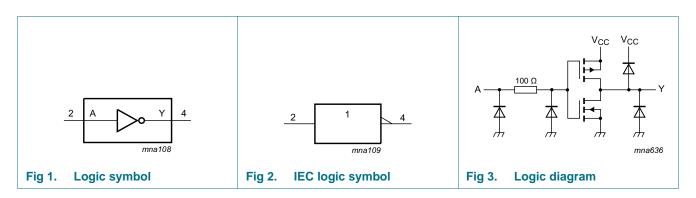
4. Marking

Table 2. Marking codes

| Type number | Marking ^[1] |
|--------------|------------------------|
| 74LVC1GU04GW | VD |
| 74LVC1GU04GV | VU4 |
| 74LVC1GU04GM | VD |
| 74LVC1GU04GF | VD |
| 74LVC1GU04GN | VD |
| 74LVC1GU04GS | VD |
| 74LVC1GU04GX | VD |

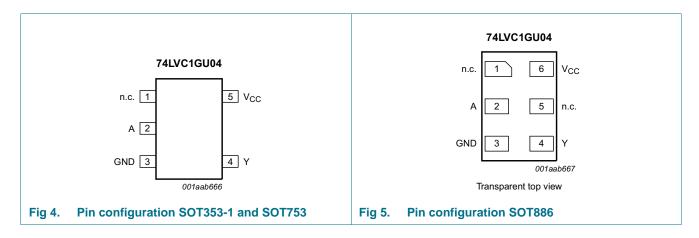
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



74LVC1GU04



6.2 Pin description

Table 3. Pin description

| Symbol | Pin | | Description |
|-----------------|---------------------------|-------|----------------|
| | TSSOP5, SC-74A and X2SON5 | XSON6 | |
| n.c. | 1 | 1 | not connected |
| Α | 2 | 2 | data input |
| GND | 3 | 3 | ground (0 V) |
| Υ | 4 | 4 | data output |
| n.c. | - | 5 | not connected |
| V _{CC} | 5 | 6 | supply voltage |

7. Functional description

Table 4. Function table [1]

| Input (A) | Output (Y) |
|-----------|------------|
| L | Н |
| Н | L |

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|--|--------|------|-----------------------|------|
| V _{CC} | supply voltage | | | -0.5 | +6.5 | V |
| I _{IK} | input clamping current | V _I < 0 V | | - | -50 | mA |
| VI | input voltage | | [1] | -0.5 | +6.5 | V |
| I _{OK} | output clamping current | $V_O > V_{CC}$ or $V_O < 0 V$ | | - | ±50 | mA |
| Vo | output voltage | Active mode | [1][2] | -0.5 | V _{CC} + 0.5 | V |
| Io | output current | $V_O = 0 V \text{ to } V_{CC}$ | | - | ±50 | mA |
| I _{CC} | supply current | | | - | +100 | mA |
| I_{GND} | ground current | | | - | -100 | mA |
| P _{tot} | total power dissipation | $T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$ | [3] | - | 250 | mW |
| T _{stg} | storage temperature | | | -65 | +150 | °C |

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|-------------------------------------|-----------------------------------|------|-----|----------|------|
| V_{CC} | supply voltage | | 1.65 | - | 5.5 | V |
| VI | input voltage | | 0 | - | 5.5 | V |
| Vo | output voltage | Active mode | 0 | - | V_{CC} | V |
| T _{amb} | ambient temperature | | -40 | - | +125 | °C |
| Δt/ΔV | input transition rise and fall rate | V _{CC} = 1.65 V to 2.7 V | 0 | - | 20 | ns/V |
| | | V _{CC} = 2.7 V to 5.5 V | 0 | - | 10 | ns/V |

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ[1] | Max | Unit |
|----------------------|---------------------------|---|-----------------------|--------|----------------------|------|
| T _{amb} = - | 40 °C to +85 °C | | | | 1 | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 1.65 V to 5.5 V | $0.75 \times V_{CC}$ | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 1.65 V to 5.5 V | - | - | $0.25 \times V_{CC}$ | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $I_{O} = -100 \mu A$; $V_{CC} = 1.65 V$ to 5.5 V | V _{CC} - 0.1 | - | - | V |
| | | $I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$ | 1.2 | - | - | V |
| | | $I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.9 | - | - | V |
| | | $I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$ | 2.2 | - | - | V |
| | | $I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.3 | - | - | V |
| | | $I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | 3.8 | - | - | V |
| V _{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V | - | - | 0.1 | V |
| | | I _O = 4 mA; V _{CC} = 1.65 V | - | - | 0.45 | V |
| | | $I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | - | - | 0.3 | V |
| | | I _O = 12 mA; V _{CC} = 2.7 V | - | - | 0.4 | V |
| | | I _O = 24 mA; V _{CC} = 3.0 V | - | - | 0.55 | V |
| | | I _O = 32 mA; V _{CC} = 4.5 V | - | - | 0.55 | V |
| I _I | input leakage current | $V_1 = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ | - | ±0.1 | ±1 | μΑ |
| I _{CC} | supply current | V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V | - | 0.1 | 4 | μΑ |
| Cı | input capacitance | V_{CC} = 3.3 V; V_I = GND to V_{CC} | - | 6 | - | pF |
| T _{amb} = - | 40 °C to +125 °C | | | | 1 | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 1.65 V to 5.5 V | $0.8 \times V_{CC}$ | - | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 1.65 V to 5.5 V | - | - | $0.2 \times V_{CC}$ | V |
| V _{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $I_O = -100 \mu A$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$ | V _{CC} - 0.1 | - | - | V |
| | | $I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$ | 0.95 | - | - | V |
| | | $I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$ | 1.7 | - | - | V |
| | | $I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$ | 1.9 | - | - | V |
| | | $I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.0 | - | - | V |
| | | $I_O = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | 3.4 | - | - | V |

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ[1] | Max | Unit |
|-----------------|--------------------------|---|-----|--------|------|------|
| V_{OL} | LOW-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | |
| | | $I_O = 100 \mu A$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$ | - | - | 0.1 | V |
| | | I _O = 4 mA; V _{CC} = 1.65 V | - | - | 0.7 | V |
| | | I _O = 8 mA; V _{CC} = 2.3 V | - | - | 0.45 | V |
| | | I _O = 12 mA; V _{CC} = 2.7 V | - | - | 0.6 | V |
| | | $I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | - | - | 0.80 | V |
| | | $I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | - | - | 0.80 | V |
| I _I | input leakage current | $V_{I} = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ | - | ±0.1 | ±1 | μА |
| I _{CC} | supply current | V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V | - | - | 4 | μΑ |

^[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 11.

| Symbol | Parameter | Conditions | -40 | °C to +85 | S °C | -40 °C to | +125 °C | Unit | |
|-----------------|-------------------------------|--|-----|-----------|------|-----------|---------|------|--|
| | | | Min | Typ[1] | Max | Min | Max | | |
| t _{pd} | propagation delay | A to Y; see Figure 8 | | | | | | | |
| | | V _{CC} = 1.65 V to 1.95 V | 0.3 | 1.7 | 5.0 | 0.3 | 6.5 | ns | |
| | | V _{CC} = 2.3 V to 2.7 V | 0.3 | 1.3 | 4.0 | 0.3 | 5.5 | ns | |
| | | V _{CC} = 2.7 V | 0.5 | 1.7 | 5.0 | 0.5 | 6.5 | ns | |
| | | V _{CC} = 3.0 V to 3.6 V | 0.5 | 1.6 | 3.7 | 0.5 | 5.0 | ns | |
| | | V _{CC} = 4.5 V to 5.5 V | 0.5 | 1.3 | 3.0 | 0.5 | 4.0 | ns | |
| C_{PD} | power dissipation capacitance | $V_I = GND \text{ to } V_{CC};$ [3] $V_{CC} = 3.3 \text{ V}$ | - | 14.9 | - | - | - | pF | |

- [1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

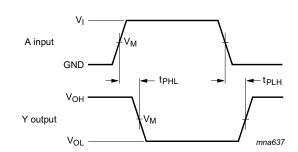
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = sum of outputs.$

12. Waveforms



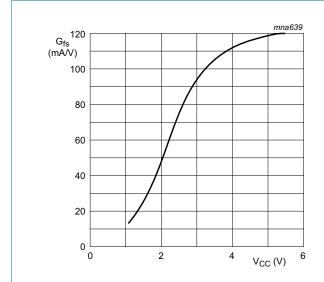
Measurement points are given in Table 9.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 8. The input A to output Y propagation delay times

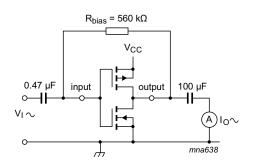
Table 9. Measurement points

| Supply voltage | Input | Output | |
|------------------|-----------------------|-----------------------|--|
| V _{CC} | V _M | V _M | |
| 1.65 V to 1.95 V | $0.5 \times V_{CC}$ | 0.5 × V _{CC} | |
| 2.3 V to 2.7 V | 0.5 × V _{CC} | 0.5 × V _{CC} | |
| 2.7 V | 1.5 V | 1.5 V | |
| 3.0 V to 3.6 V | 1.5 V | 1.5 V | |
| 4.5 V to 5.5 V | 0.5 × V _{CC} | 0.5 × V _{CC} | |



 $T_{amb} = 25 \, ^{\circ}C.$

Fig 9. Typical forward transconductance as a function of supply voltage

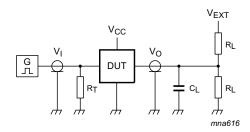


$$G_{fs} = \frac{\Delta I_O}{\Delta V_I}$$

 $f_i = 1 \text{ kHz at } V_O \text{ is constant}$

Fig 10. Test set-up for measuring forward transconductance

Unbuffered inverter



Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 11. Test circuit for measuring switching times

Table 10. Test data

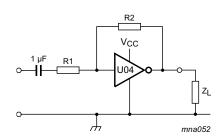
| Supply voltage | Input | | Load | | V _{EXT} |
|------------------|-----------------|-------------|-------|----------------|-------------------------------------|
| V _{CC} | VI | $t_r = t_f$ | | R _L | t _{PLH} , t _{PHL} |
| 1.65 V to 1.95 V | V _{CC} | ≤ 2.0 ns | 30 pF | 1 kΩ | open |
| 2.3 V to 2.7 V | V _{CC} | ≤ 2.0 ns | 30 pF | 500 Ω | open |
| 2.7 V | 2.7 V | ≤ 2.5 ns | 50 pF | 500 Ω | open |
| 3.0 V to 3.6 V | 2.7 V | ≤ 2.5 ns | 50 pF | 500 Ω | open |
| 4.5 V to 5.5 V | V _{CC} | ≤ 2.5 ns | 50 pF | 500 Ω | open |

13. Application information

Some applications are:

- Linear amplifier (see Figure 12)
- In crystal oscillator design (see Figure 13)

Remark: All values given are typical unless otherwise specified.



 $V_{o(p-p)} = V_{CC} - 1.5 \text{ V}$ centered at $0.5V_{CC}$.

$$A_u = -\frac{G_{OL}}{I + \frac{RI}{R2}(I + G_{OL})}$$

 G_{OL} = loop gain.

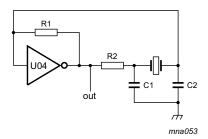
 A_u = voltage amplification.

 $R1 \ge 3 \text{ k}\Omega, R2 \le 1 \text{ M}\Omega$

 $Z_L > 10 \text{ k}\Omega; A_{OL} = 20 \text{ (typ.)}$

Typical unity gain bandwidth product is 5 MHz.

Fig 12. Used as a linear amplifier



C1 = 47 pF (typ.)

C2 = 22 pF (typ.)

R1 = 1 M Ω to 10 M Ω (typ.)

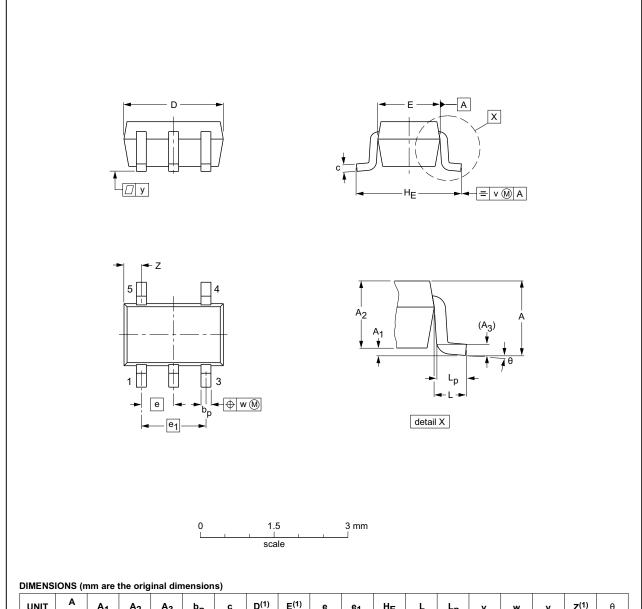
R2 optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} is typically 2 mA at V_{CC} = 3.3 V and f = 10 MHz).

Fig 13. Crystal oscillator configuration

14. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



| UNIT | A max. | A ₁ | A ₂ | A ₃ | bp | С | D ⁽¹⁾ | E ⁽¹⁾ | е | e ₁ | HE | L | Lp | v | * | у | Z ⁽¹⁾ | θ |
|------|-----------|----------------|----------------|----------------|--------------|--------------|------------------|------------------|------|----------------|-------------|-------|--------------|-----|-----|-----|------------------|----------|
| mm | 1.1 | 0.1 0 | 1.0 0.8 | 0.15 | 0.30 0.15 | 0.25 0.08 | 2.25 1.85 | 1.35 1.15 | 0.65 | 1.3 | 2.25 2.0 | 0.425 | 0.46 0.21 | 0.3 | 0.1 | 0.1 | 0.60 0.15 | 7° 0° |

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

| OUTLINE | REFERENCES | | | EUROPEAN | ISSUE DATE | |
|----------|------------|--------|--------|----------|------------|-----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT353-1 | | MO-203 | SC-88A | | | -00-09-01- 03-02-19 |

Fig 14. Package outline SOT353-1 (TSSOP5)

74LVC1GU04

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Plastic surface-mounted package; 5 leads

SOT753

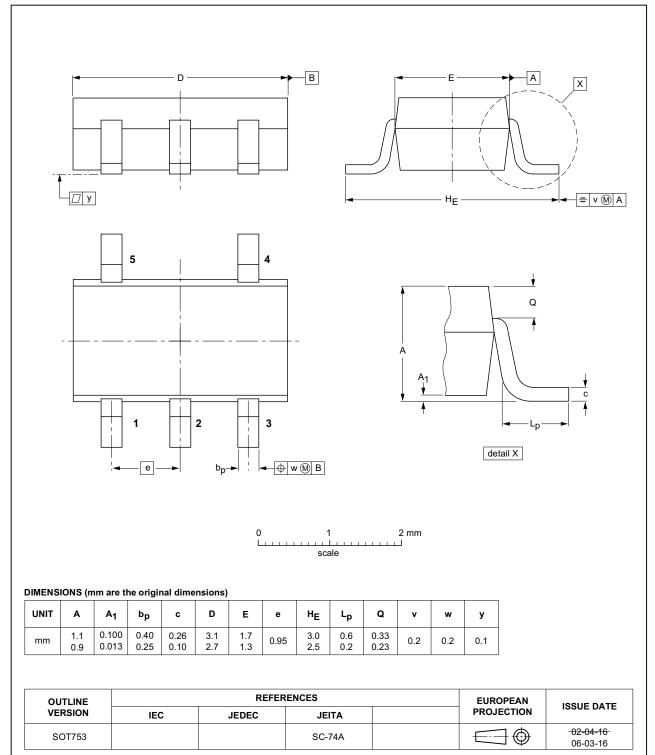


Fig 15. Package outline SOT753 (SC-74A)

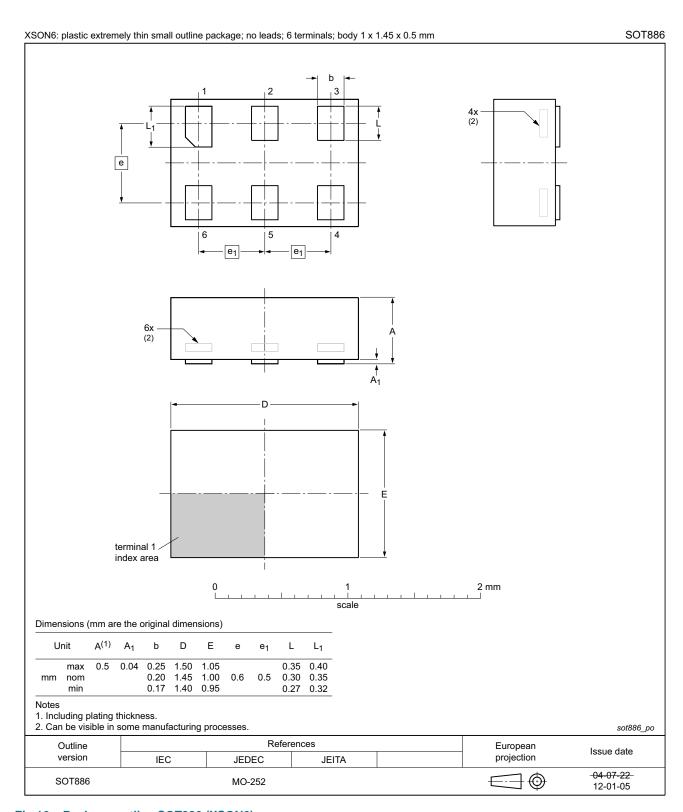


Fig 16. Package outline SOT886 (XSON6)

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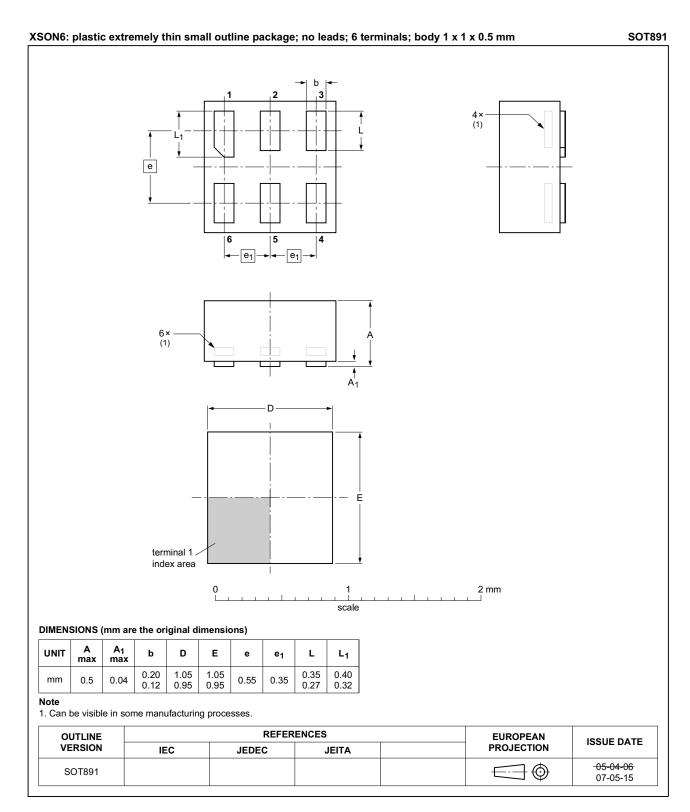


Fig 17. Package outline SOT891 (XSON6)

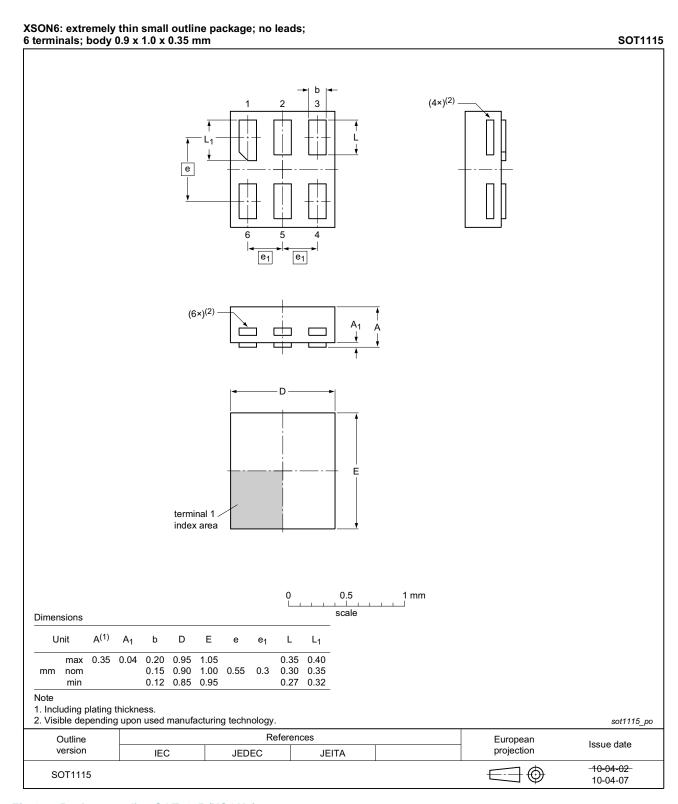


Fig 18. Package outline SOT1115 (XSON6)

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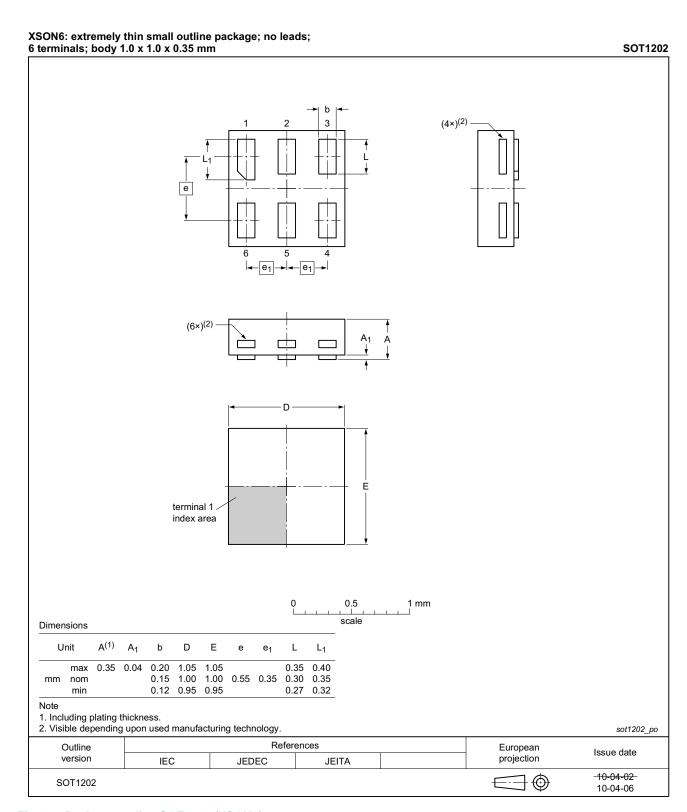


Fig 19. Package outline SOT1202 (XSON6)

Product data sheet

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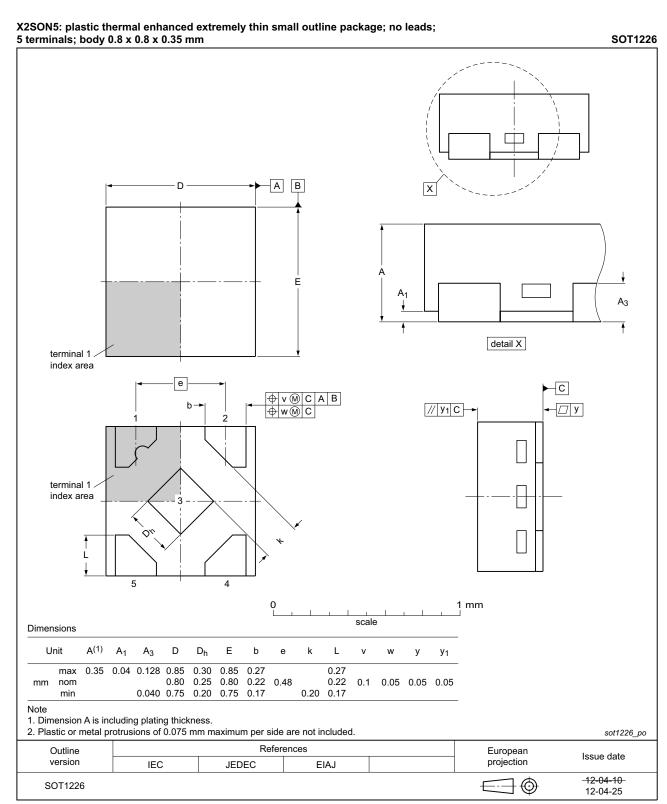


Fig 20. Package outline SOT1226 (X2SON5)

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Unbuffered inverter

15. Abbreviations

Table 11. Abbreviations

| Acronym | Description |
|---------|---|
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| НВМ | Human Body Model |
| MM | Machine Model |

16. Revision history

Table 12. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|-----------------|--|-----------------------|---------------|-----------------|--|
| 74LVC1GU04 v.13 | 20161212 | Product data sheet | - | 74LVC1GU04 v.12 | |
| Modifications: | • Table 7: The maximum limits for leakage current and supply current have c | | | ave changed. | |
| 74LVC1GU04 v.12 | 20130409 | Product data sheet | - | 74LVC1GU04 v.11 | |
| Modifications: | Descriptive title changed to Unbuffered inverter. | | | | |
| 74LVC1GU04 v.11 | 20120702 | Product data sheet | - | 74LVC1GU04 v.10 | |
| Modifications: | Added type number 74LVC1GU04GX (SOT1226) | | | | |
| | Package outline drawing of SOT886 (<u>Figure 16</u>) modified. | | | | |
| 74LVC1GU04 v.10 | 20111201 | Product data sheet | - | 74LVC1GU04 v.9 | |
| Modifications: | Legal pages updated. | | | | |
| 74LVC1GU04 v.9 | 20101021 | Product data sheet | - | 74LVC1GU04 v.8 | |
| 74LVC1GU04 v.8 | 20070612 | Product data sheet | - | 74LVC1GU04 v.7 | |
| 74LVC1GU04 v.7 | 20061006 | Product data sheet | - | 74LVC1GU04 v.6 | |
| 74LVC1GU04 v.6 | 20040921 | Product specification | - | 74LVC1GU04 v.5 | |
| 74LVC1GU04 v.5 | 20040628 | Product specification | - | 74LVC1GU04 v.4 | |
| 74LVC1GU04 v.4 | 20030630 | Product specification | - | 74LVC1GU04 v.3 | |
| 74LVC1GU04 v.3 | 20030212 | Product specification | - | 74LVC1GU04 v.2 | |
| 74LVC1GU04 v.2 | 20010406 | Product specification | - | 74LVC1GU04 v.1 | |
| 74LVC1GU04 v.1 | 20001212 | Product specification | - | - | |

17. Legal information

17.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

17.2 Definitions

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